505219626 12/04/2018

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 EPAS ID: PAT5266394 Stylesheet Version v1.2

SUBMISSION TYPE: NEW ASSIGNMENT

NATURE OF CONVEYANCE: ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
Po-Chang Lin	11/22/2018
Bo-Han Huang	11/22/2018
Chih-Chung Chen	11/22/2018
Chun-Hsien Lin	11/22/2018
Shih-Hung Tsai	11/22/2018
Po-Kuang Hsieh	11/22/2018

RECEIVING PARTY DATA

Name:	UNITED MICROELECTRONICS CORP.
Street Address:	No.3, Li-Hsin Road 2, Science-Based Industrial Park
City:	Hsin-Chu City
State/Country:	TAIWAN

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	16209890

CORRESPONDENCE DATA

Fax Number: (703)997-4517

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

Phone: 3027291562

Email: Patent.admin.uspto.cr@naipo.com

Correspondent Name: WINSTON HSU

Address Line 1: 5F., NO.389, FUHE RD., YONGHE DIST.,

Address Line 4: NEW TAIPEI CITY, TAIWAN

ATTORNEY DOCKET NUMBER: NAUP3364USA

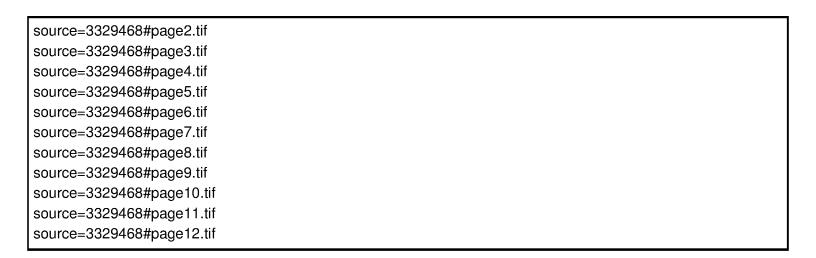
NAME OF SUBMITTER: STEFFI CHANG

SIGNATURE: /STEFFI CHANG/

DATE SIGNED: 12/04/2018

Total Attachments: 12 source=3329468#page1.tif

PATENT 505219626 REEL: 047673 FRAME: 0212



PATENT REEL: 047673 FRAME: 0213

Title of Invention:

METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

As the below named inventor, I here This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nu	mber	filed on	, or
☐ PCT international application	n number	filed on	
The above-identified application was	made or authorized to be made	by me.	
I believe that I am the original invente application.	or or an original joint inventor of a	claimed invention in the	
I hereby acknowledge that any willful under18 U.S.C. 1001 by fine or impri	false statement made in this dec sonment of not more than five (5)	laration is punishable years, or both.	
	UNITED MICROELECTRON CORP.	IICS having a postal a	ddress of
No.3, Li-Hsin Road 2, Science	-Based Industrial Park, Hsi	n-Chu City 300, Taiw	an, R.O.C.
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an	I of the sum of One Dollar (\$ 1.0 d valuable consideration.	0), the receipt of which is	hereby
I hereby sell, assign and transfer to A the entire right, title and interest in ar invention as above-identified application or substitutes, or extensions thereof, and	nd to any and all improvements w tion and, in and to, all Letters Pate any continuations, continuation-i	hich are disclosed in the ent to be obtained for said n-part, divisions, renewals	j S.
I hereby covenant that no assignment entered into which would conflict with	nt, sale, agreement or encumbran n this assignment;	ce has been or will be ma	de or
I further covenant that ASSIGNEE wi and documents relating to said inven known and accessible to I and will te- related thereto and will promptly exec	tion and said Letters Patent and I stify as to the same in any interfe	egal equivalents as may be rence, litigation proceeding	oe
representatives any and all papers, in maintain, issue and enforce said app equivalents thereof which may be ne IN WITNESS WHEREOF, I have her	lication, said invention and said L cessary or desirable to carry out t	etters Patent and said	
Note: An application data sheet (PTC inventive entity, must accompany this	0/SB/14 or equivalent), including r s form. Use this form for <u>each ado</u>	naming the entire ditional inventor.	

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NPO#NAU-P3364-USA:0 CUST#UMCD-2018-0393

Inventor: Po-Chang Lin Date: NOV 2 2 2018

Signature: Po-Chang Lin

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NPO#NAU-P3364-USA:0 CUST#UMCD-2018-0393

Title of Invention: METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

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In consideration of the payment by	UNITED MICROELEC	TRONICS having a p	postal address of
No.3, Li-Hsin Road 2, Science	-Based Industrial Par	k, Hsin-Chu City 300,	Taiwan, R.O.C
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an	o I of the sum of One Dolla d valuable consideration.	r (\$ 1.00), the receipt of w	hich is hereby
I hereby sell, assign and transfer to A the entire right, title and interest in ar invention as above-identified applica- invention by the above application or substitutes, or extensions thereof, an	nd to any and all improvem tion and, in and to, all Lette any continuations, continu	nents which are disclosed it ers Patent to be obtained to uation-in-part, divisions, re	in the for said enewals.
I hereby covenant that no assignment entered into which would conflict with	nt, sale, agreement or encu n this assignment;	umbrance has been or will	be made or
I further covenant that ASSIGNEE wand documents relating to said invenknown and accessible to I and will te related thereto and will promptly executed.	tion and said Letters Pater stify as to the same in any	nt and legal equivalents as interference, litigation pro	s mav be
representatives any and all papers, in maintain, issue and enforce said app equivalents thereof which may be ne IN WITNESS WHEREOF, I have her	lication, said invention and cessary or desirable to car	d said Letters Patent and s	said of.
Note: An application data sheet (PTC	D/SB/14 or equivalent), incl	luding naming the entire	

Page 3 of 12

inventive entity, must accompany this form. Use this form for each additional inventor.

NPO#NAU-P3364-USA:0 CUST#UMCD-2018-0393

LEGAL NA	ME OF INVENTOR(ASSIGNOR)			
Inventor:	Bo-Han Huang	Date:	NOV 2 2 2018	
Signature:	Bollan Hunna			
	7010			

Page 4 of 12

NPO#NAU-P3364-USA:0 CUST#UMCD-2018-0393

Title of Invention:

METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

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I hereby covenant that no assignment entered into which would conflict with	t, sale, agreement or encumbran this assignment;	ce has been or will be made	or
I further covenant that ASSIGNEE will and documents relating to said invent known and accessible to I and will tes related thereto and will promptly exec	tion and said Letters Patent and I stify as to the same in any interfe	egal equivalents as may be rence, litigation proceeding	cts
representatives any and all papers, in maintain, issue and enforce said appl equivalents thereof which may be need IN WITNESS WHEREOF, I have here	ication, said invention and said L cessary or desirable to carry out t	etters Patent and said the proposes thereof.	
Note: An application data sheet (PTO inventive entity, must accompany this	/SB/14 or equivalent), including r form. Use this form for <u>each ado</u>	naming the entire litional inventor.	

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NPO#NAU-P3364-USA:0 CUST#UMCD-2018-0393

Inventor: Chih-Chung Chen Date: NOV 2 2 2018

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Title of Invention:

METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

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I hereby covenant that no assignmer entered into which would conflict with	nt, sale, agreement or encumbrand n this assignment;	ce has been or will be made	or
I further covenant that ASSIGNEE w and documents relating to said inven known and accessible to I and will te related thereto and will promptly exec	ition and said Letters Patent and le stify as to the same in any interfer	egal equivalents as may be ence. litigation proceeding	ts
representatives any and all papers, is maintain, issue and enforce said app equivalents thereof which may be ne IN WITNESS WHEREOF, I have her	lication, said invention and said Locessary or desirable to carry out t	etters Patent and said he proposes thereof	
Note: An application data sheet (PTC inventive entity, must accompany this	D/SB/14 or equivalent), including n s form. Use this form for <u>each add</u>	aming the entire	

Page 7 of 12

NPO#NAU-P3364-USA:0 CUST#UMCD-2018-0393

LEGAL NAME OF INVENTOR(ASSIGNOR)				
Inventor:	Chun-Hsien Lin		Date:	NOV 2 2 2018
Signature:	Chun-Hsien	Lon		

Page 8 of 12

NPO#NAU-P3364-USA:0 CUST#UMCD-2018-0393

Title of Invention: METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

As the below named inventor, I hereby declare that: This declaration is directed to:		
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☐ United States application number	_filed on, o)r
☐ PCT international application number	filed on	
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(referred to as "ASSIGNEE"below) to I of the sum of One Dollar (\$ 1.0 acknowledged, and for other good and valuable consideration.	00), the receipt of which is here	by
I hereby sell, assign and transfer to ASSIGNEE and the successors at the entire right, title and interest in and to any and all improvements vinvention as above-identified application and, in and to, all Letters Painvention by the above application or any continuations, continuation-substitutes, or extensions thereof, and as to Letters Patent any reissu	vhich are disclosed in the tent to be obtained for said in-part, divisions, renewals	Ξ
I hereby covenant that no assignment, sale, agreement or encumbrar entered into which would conflict with this assignment;	nce has been or will be made or	•
I further covenant that ASSIGNEE will, upon its request, be provided and documents relating to said invention and said Letters Patent and known and accessible to I and will testify as to the same in any interferelated thereto and will promptly execute and deliver to ASSIGNEE or	legal equivalents as may be erence. litigation proceeding	
representatives any and all papers, instruments or affidavits required maintain, issue and enforce said application, said invention and said lequivalents thereof which may be necessary or desirable to carry out IN WITNESS WHEREOF, I have hereunto set hand and seal this on the same of the same and seal this on the same of the sam	Letters Patent and said the proposes thereof	

Page 9 of 12

Note: An application data sheet (PTO/SB/14 or equivalent), including naming the entire inventive entity, must accompany this form. Use this form for <u>each additional inventor</u>.

NPO#NAU-P3364-USA:0 CUST#UMCD-2018-0393

LEGAL NAME OF INVENTOR(ASSIGNOR)			
Inventor:	Shih-Hung Tsai	Date:	NOV 2 2 2018
Signature:	Stal-Hung Toni		

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NPO#NAU-P3364-USA:0 CUST#UMCD-2018-0393

F#NPO-P0002E-US1201 DSB0-107U028885

PATENT REEL: 047673 FRAME: 0223

Title of Invention: METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

As the below named inventor, I hereb This declaration is directed to:	y declare that:		
The attached application, or			
☐ United States application nu	mber	filed on,	or
☐ PCT international application	number	filed on	
The above-identified application was	made or authorized to be made	by me.	
I believe that I am the original invento application.	or or an original joint inventor of	a claimed invention in the	
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No.3, Li-Hsin Road 2, Science-	Based Industrial Park, Hs	in-Chu City 300, Taiwan,	R.O.C
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good and	I of the sum of One Dollar (\$ 1. I valuable consideration.	00), the receipt of which is her	eby
I hereby sell, assign and transfer to Athe entire right, title and interest in and invention as above-identified application invention by the above application or a substitutes, or extensions thereof, and	d to any and all improvements v on and, in and to, all Letters Pa any continuations, continuation-	which are disclosed in the tent to be obtained for said in part, divisions, renewals	ΞE
I hereby covenant that no assignment entered into which would conflict with	, sale, agreement or encumbra this assignment;	nce has been or will be made o	or
I further covenant that ASSIGNEE will and documents relating to said inventi known and accessible to I and will tes related thereto and will promptly exec	ion and said Letters Patent and tifv as to the same in any interfe	legal equivalents as may be erence. litigation proceeding	s
representatives any and all papers, in maintain, issue and enforce said appli equivalents thereof which may be nec IN WITNESS WHEREOF, I have here	cation, said invention and said essary or desirable to carry out	Letters Patent and said	
Note: An application data sheet (PTO/	SB/14 or equivalent), including	naming the entire	

Page 11 of 12

inventive entity, must accompany this form. Use this form for each additional inventor.

NPO#NAU-P3364-USA:0 CUST#UMCD-2018-0393

LEGAL NAME OF INVENTOR(ASSIGNOR)					
Inventor:	Po-Kuang Hsieh		Date:	NOV 2 2 2018	
Signature:	Po-kuang	Hsieh			_

Page 12 of 12

NPO#NAU-P3364-USA:0 CUST#UMCD-2018-0393

RECORDED: 12/04/2018

F#NPO-P0002E-US1201 DSB0-107U028885

PATENT REEL: 047673 FRAME: 0225